



DMT3020LFDB

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
2017	20mΩ @ V <sub>GS</sub> = 10V	7.7A
30V	32mΩ @ V <sub>GS</sub> = 4.5V	6.1A

## Description

This new generation MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

## Applications

- General Purpose Interfacing Switch
- **Power Management Functions**

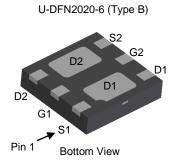
### DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

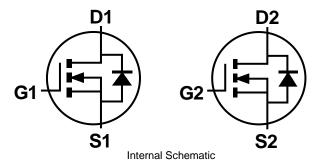
## **Features and Benefits**

- 0.6mm Profile Ideal for Low Profile Applications
- Low Gate Threshold Voltage
- Low On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

# **Mechanical Data**

- Case: U-DFN2020-6 •
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)





## Ordering Information (Note 4)

	Part Number	Case	Packaging				
	DMT3020LFDB-7	U-DFN2020-6 (Type B)	3,000/Tape & Reel				
	DMT3020LFDB-13	U-DFN2020-6 (Type B)	10,000/Tape & Reel				
Notes:	1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.						

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



# **Marking Information**

Site 1



Y2 = Product Type Marking Code YM = Date Code MarkingY = Year (ex: F = 2018)M = Month (ex: 9 = September)

Date Code Key												
Year	201	5	2016		2017	20	18	2019		2020	2	2021
Code	С		D		E	F	-	G		Н		
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Site 2



Y2 = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 8 = 2018)

W = Week (ex: a = week 27; z represents week 52 and 53)X = Internal Code (ex: U = Monday)

Date Code Key								
Year	2018	2019	2020	2021	2022	2023	2024	2025
Code	8	9	0	1	2	3	4	5
Week	1-26			27-52				3
Code	A-Z			A-Z a-z z				
Internal Code	Sun	Mon	Tue	,	Wed	Thu	Fri	Sat
Code	Т	U	V		W	Х	Y	7



# **Maximum Ratings** ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V <sub>DSS</sub>	30	V		
Gate-Source Voltage	V <sub>GSS</sub>	±20	V		
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +75°C	ID	7.7 6.2	А
Maximum Continuous Body Diode Forward Curre	Is	2	А		
Pulsed Drain Current (380µs Pulse, Duty Cycle =	I <sub>DM</sub>	50	A		

# **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	0.7	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	170	°C/W
Total Power Dissipation (Note 6)		PD	1.8	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	70	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	—	_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current TJ = +25°C	IDSS		—	1	μA	$V_{DS} = 24V, V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>		—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.0	—	2.5	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$
Static Drain-Source On-Resistance				20	mΩ	$V_{GS} = 10V, I_D = 9.0A$
	R <sub>DS(ON)</sub>	_	_	32	11152	$V_{GS} = 4.5V, I_D = 7.0A$
Diode Forward Voltage	V <sub>SD</sub>	_	—	1.0	V	$V_{GS} = 0V, I_S = 2A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	_	393	—	pF	
Output Capacitance	Coss		173	—	pF	─ V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, ─ f = 1.0MHz
Reverse Transfer Capacitance	Crss		27	—	pF	1 = 1.00112
Gate Resistance	R <sub>G</sub>	—	1.1	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge (V <sub>GS</sub> = 10V)	$Q_G$	_	7.0	—	nC	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>G</sub>	—	3.6	—	nC	עם = 15V. א = 9A
Gate-Source Charge	Q <sub>GS</sub>	—	0.9	—	nC	$v_{DD} = 15v, I_D = 9A$
Gate-Drain Charge	$Q_{GD}$	—	1.5	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	_	1.8	—	ns	
Turn-On Rise Time	t <sub>R</sub>	—	1.9	—	ns	V <sub>DD</sub> = 15V, V <sub>GS</sub> = 10V,
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	7.5	—	ns	$R_G = 6\Omega, I_D = 9A$
Turn-Off Fall Time	t <sub>F</sub>		2.4	_	ns	
Reverse Recovery Time	t <sub>RR</sub>		10	—	ns	
Reverse Recovery Charge	Q <sub>RR</sub>		2.6	_	nC	I <sub>F</sub> = 9A, di/dt = 100A/μs

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

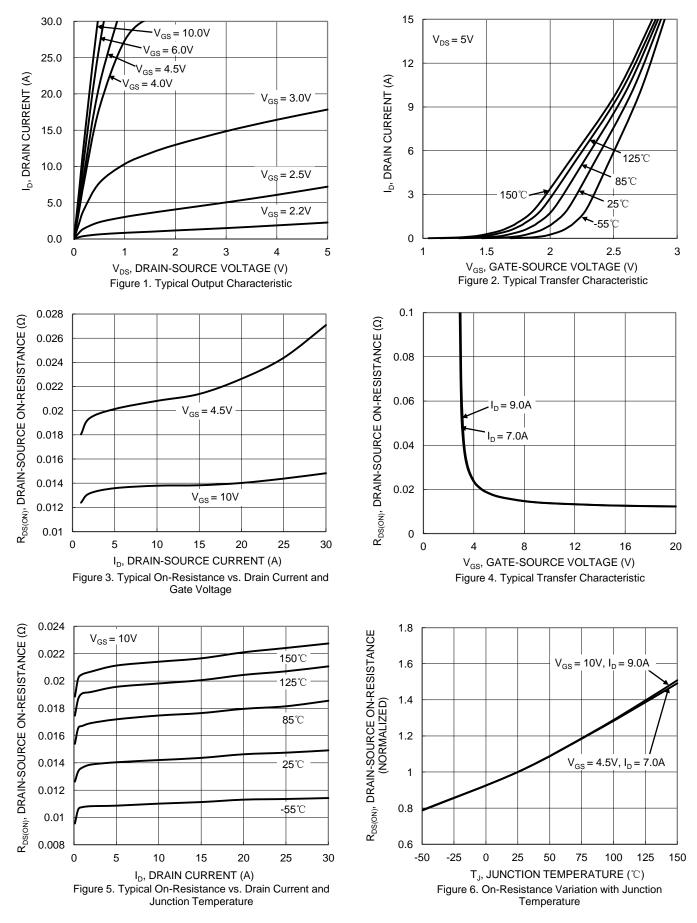
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.

7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.

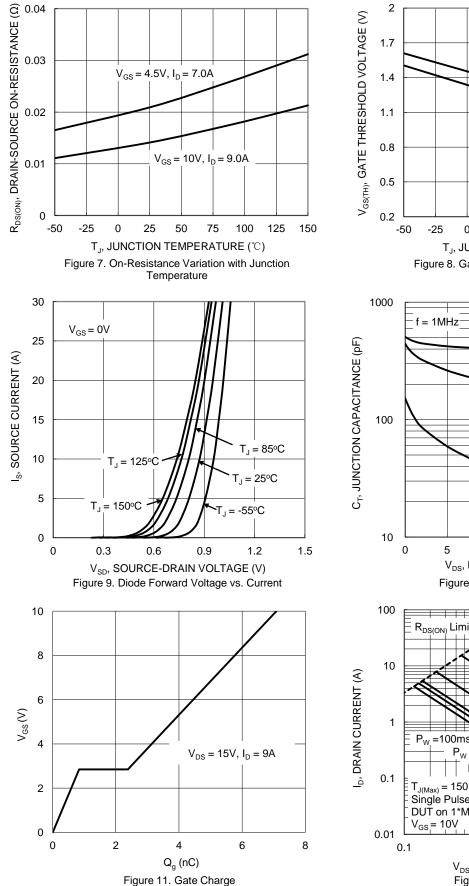


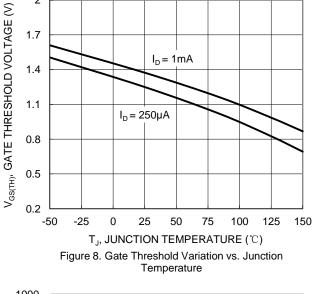
# DMT3020LFDB

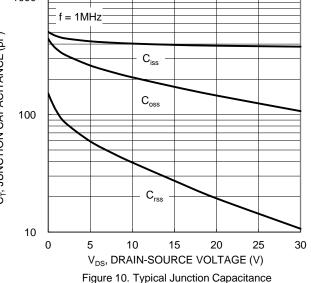




# DMT3020LFDB







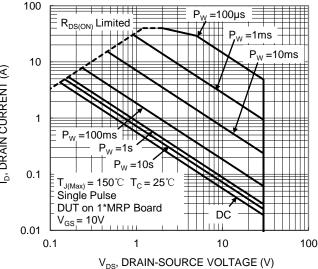
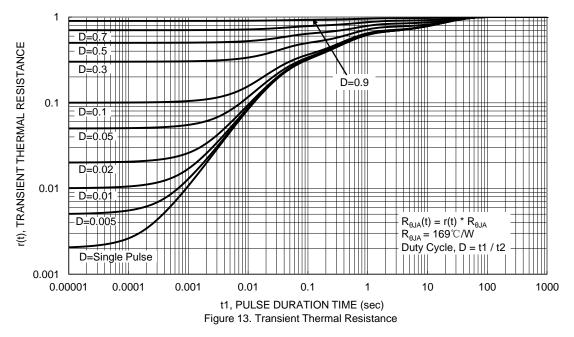


Figure 12. SOA, Safe Operation Area

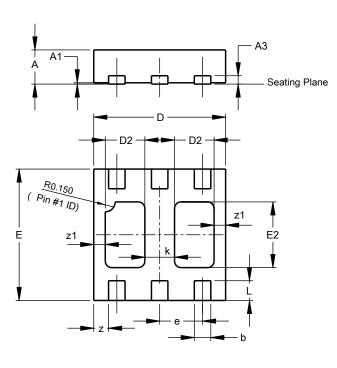






## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.



	U-DFN2020-6 Type B									
Dim										
Α	0.545	0.605	0.575							
A1	0.00	0.05	0.02							
A3	-	-	0.13							
b	0.20	0.30	0.25							
D	1.95	2.075	2.00							
D2	0.50	0.70	0.60							
е	-	-	0.65							
Е	1.95	2.075	2.00							
E2	0.90	1.10	1.00							
k	-	-	0.45							
L	0.25	0.35	0.30							
z	-	-	0.225							
z1	-	-	0.175							
All	Dimens	ions in	mm							

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

 $Y_{2} Y_{1}(2x)$ 

Dimensions	Value (in mm)
С	0.650
G	0.150
G1	0.450
Х	0.350
X1	0.600
X2	1.650
Ŷ	0.500
Y1	1.000
Y2	2.300

U-DFN2020-6 (Type B)

U-DFN2020-6 (Type B)



#### **IMPORTANT NOTICE**

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

#### LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
  - 1. are intended to implant into the body, or
  - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2018, Diodes Incorporated

www.diodes.com